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TECHNOLOGY CENTER 2800

To:	Examiner K. Addison	From: Christopher A. Bennett
Fax:	703-872-9318	<b>Date:</b> July 29, 2003
Phone	703-306-5855	Pages: 11
Re:	09/840,359	CC:
	36856.472	

## ·Comments:

Examiner Addison,

Please find attached the following documents for the above-identified application:

- A Request for Reconsideration;
- A three-month Petition for Extension of Time; and
- A Credit Card Form in the amount of \$930.00;

Respectfully submitted,

Christopher A. Bennett

**KEATING & BENNETT, LLP** (Registration Number 46,710)

## CERTIFICATE OF FACSIMILE TRANSMISSION

I hereby certify that this correspondence is being transmitted to Group Art Unit 2834, 703-872-9318, addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

Date: July 29, 2003

Sonia V. McVean

**PATENT** 36856.472

## IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant: Hajime KANDOU et al.

Serial No.: 09/840,359

Filed: April 23, 2001

Title: SURFACE ACOUSTICE WAVE DEVICE

Art Unit: 2834

Examiner: K. Addison

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## **REQUEST FOR RECONSIDERATION**

**TECHNOLOGY CENTER 2800** 

Assistant Commissioner for Patents Washington, D.C. 20231

Sir:

In response to the Office Action dated January 29, 2003, the period for response to which has been extended to July 29, 2003, by the accompanying Petition for Three-Month Extension of Time, please reconsider the above-identified application in view of the following remarks.

Claims 1 and 3-14 are pending in this application.

Claims 1 and 3-14 were rejected under 35 U.S.C. § 103(a) as being unpatentable over Kadota et al. (U.S. 5,432,392) in view of Kadota ("Combination of ZnO Film and Quartz to Realize Large Coupling Factor and Excellent Temperature Coefficient for SAW Devices"). Applicants respectfully traverse this rejection.

Claim 1 recites:

"A surface acoustic wave device, comprising:

a quartz substrate;

a piezoelectric thin film disposed on said quartz substrate;

comb electrodes disposed between said quartz substrate and said piezoelectric thin film; and

the normalized film thickness H/ $\lambda$  of said piezoelectric thin film is at least about 0.20, wh rein the film thickness f said piezo lectric thin film i H, and th wavelength of a urfac acoustic wav is  $\lambda$ ."